

In the Specification:

At page 2, lines 1-11, please amend the paragraph as follows:

While SOI structures have been found useful in reducing the capacitance typically associated with conventional silicon applications, the epitaxial silicon in the SOI structure exhibits relatively low carrier mobility. Germanium is an example material that can be a desirable alternative to silicon for a variety of applications, largely because germanium exhibits a carrier mobility that is very high relative to that in silicon. For instance, germanium is a promising channel material for MOS-type transistors due to this high carrier mobility. Germanium also has other material properties that differ from silicon, such as a smaller bandgap. These properties facilitate optoelectronic devices and many additional device options. In the past few decades, the use of germanium as well as other materials for integrated circuit applications have been investigated and implemented due to their enhanced qualities, relative to other types of semiconductor materials such as silicon.